

This listing of the claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (Currently amended) A method of forming a microelectronic structure comprising:

providing a substrate comprising source/drain and gate regions,

wherein the gate region comprises a metal gate disposed on a high k gate dielectric layer, and

laser annealing the substrate ,wherein the metal gate does not substantially diffuse into the high k gate dielectric layer.
2. (Previously presented) The method of claim 1 further comprising wherein the metal gate comprises a work function from about 3.9 electron volts to about 5.2 electron volts that is disposed on the gate dielectric layer.
3. (Canceled)
4. (Previously presented) The method of claim 1 further comprising wherein the metal gate does not substantially diffuse into a polysilicon layer disposed on the metal gate.
5. (Previously presented) The method of claim 1 wherein laser annealing the substrate comprises exposing the substrate to a laser beam for a time sufficient to activate an

implanted species.

6. (Original) The method of claim 1 wherein laser annealing the substrate comprises exposing the substrate to a laser beam pulsed at about 20 nanosecond intervals or less.

7. (Original) The method of claim 1 wherein laser annealing the substrate comprises activating an implanted species in the source/drain regions by laser annealing.

8. (Previously presented) The method of claim 7 further comprising wherein the ratio of the depth of the source/drain regions to the length of the source/drain regions is less than about 1:2.

9. (Canceled)

10. (Previously presented) The method of claim 1 further comprising wherein the metal gate is selected from the group consisting of tungsten, platinum, ruthenium, palladium, molybdenum and niobium, and their alloys, metal carbides, metal nitrides, metal carbides and conductive metal oxides.

11. (Currently amended) A method of forming a microelectronic structure comprising;
providing a substrate comprising doped source/drain and gate regions,

wherein the gate region comprises a metal gate disposed on a high k dielectric layer, and wherein the metal gate comprises a work function approximately equal to a work function of n doped polysilicon; and

forming shallow source/drain regions by laser annealing the substrate,
wherein the metal gate does not substantially diffuse into the high k gate dielectric layer.

12. (Original) The method of claim 11 wherein forming shallow source/drain regions comprises forming source/drain regions wherein the ratio of the depth of the source/drain regions to the length of the source/drain regions is less than about 1:2.

13. (Previously presented) The method of claim 11 further comprising wherein the metal gate comprises a work function from about 3.9 to about 4.2 electron volts.

14. (Previously presented) The method of claim 11 further comprising wherein the metal gate comprises a work function approximately equal to a work function of p doped polysilicon.

15. (Previously presented) The method of claim 11 further comprising wherein the metal gate comprises a work function from about 4.8 to about 5.1 electron volts.

16. (Previously presented) The method of claim 11 further comprising wherein the high k dielectric layer selected from the group consisting of hafnium oxide, zirconium oxide, titanium oxide, and aluminum oxide and /or combinations thereof.

Claims 17-24 (Canceled).